



Features

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitance
- Easy to Parallel and Simple to Drive

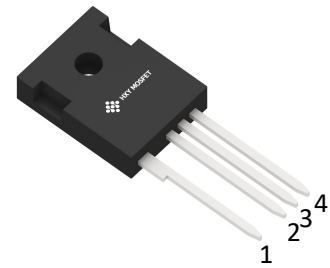
Benefits

- Higher system efficiency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

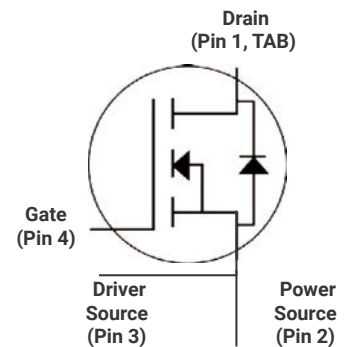
Applications

- Renewable energy
- EV battery chargers
- High voltage DC/DC converters
- Switch Mode Power Supplies

Ordering Part Number	Package	Marking
C3M0015120K	TO-247-4L	C3M0015120K



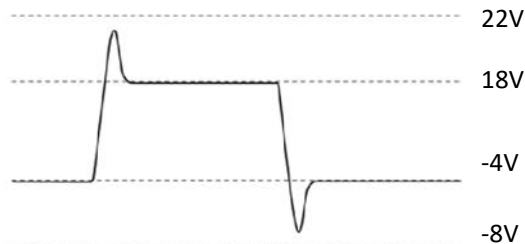
TO-247-4L



Maximum Ratings (T_c = 25 °C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DS}	1200	V
Continuous drain current T _c = 25°C T _c = 100°C	I _D	117 84	A
Pulsed drain current (T _c = 25°C, t _p limited by T _{jmax})	I _D pulse	250	A
Gate-Source voltage	V _{GS}	-4/+18	V
Gate-Source voltage (dynamic, Absolute maximum values)	V _{GSmax}	-8/+22	V
Power dissipation (T _c = 25°C)	P _{tot}	556	W
Operating junction and storage temperature	T _j , T _{stg}	-55...+175	°C

- Example of acceptable V_{GS} waveform





Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case. Max	R_{thJC}	0.27	°C/W
Thermal resistance, junction – ambient. Max	R_{thJA}	40	

Electrical Characteristic (at $T_j = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition	
		min.	typ.	max.			
Static Characteristic							
Drain-source breakdown voltage	BV _{DSS}	1200	-	-	V	V _{GS} =0V, I _D =250uA	
Gate threshold voltage	V _{GS(th)}	2	-	4	V	V _{DS} =V _{GS} ,I _D =25mA	
Zero gate voltage drain current	I _{DSS}	- -	1 10	50 -	μA	V _{DS} =1200V,V _{GS} =0V T _J =25°C T _J =175°C	
Gate-source leakage current	I _{GSS}	-		200	nA	V _{GS} =18V,V _{DS} =0V	
Drain-source on-state resistance	R _{DS(on)}	- -	33 50	49 -	mΩ	V _{GS} =20V, I _D =80A, T _J =25°C T _J =175°C	
Transconductance	g _{fs}	-	27	-	S	V _{DS} =20V,I _D =40A	
Dynamic Characteristic							
Input Capacitance	C _{iss}	-	4508	-	pF	V _{DS} = 1000V V _{GS} = 0V T _J = 25°C V _{AC} = 25mV f = 1MHz	
Output Capacitance	C _{oss}	-	214	-			
Reverse Transfer Capacitance	C _{rss}	-	26	-			
Gate Total Charge	Q _G	-	222	-	nC	V _{DS} = 800V V _{GS} = -0/18V I _D = 80A	
Gate-Source charge	Q _{gs}	-	46.4	-			
Gate-Drain charge	Q _{gd}	-	77.6	-			
Turn-On Switching Energy	E _{ON}	-	2290	-	μJ	V _{DD} = 800V V _{GS} = -4/+18V I _D = 80A R _G = 5Ω L = 120uH	
Turn-Off Switching Energy-	E _{OFF}	-	630				
Turn-on delay time	t _{d(on)}	-	49.2	-	ns		
Rise time	t _r	-	14.2	-			
Turn-off delay time	t _{d(off)}	-	21.7	-			
Fall time	t _f	-	11.3	-			
Gate resistance	R _G	-	0.9	-	Ω		V _{AC} = 25mV, f=1MHz



Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}		4.4		V	$V_{GS}=0V, I_{SD}=40A,$ $T_J=25^{\circ}C$
			3.9			$V_{GS}=0V, I_{SD}=40A,$ $T_J=175^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	29.6	-	ns	$V_R = 400V,$ $I_D = 80A$ $di/dt = 1000A/\mu S$
Body Diode Reverse Recovery Charge	Q_{rr}	-	272	-	nC	



Typical Performance Characteristics

Fig 1. Output Characteristic ($T_J = -55^\circ\text{C}$)

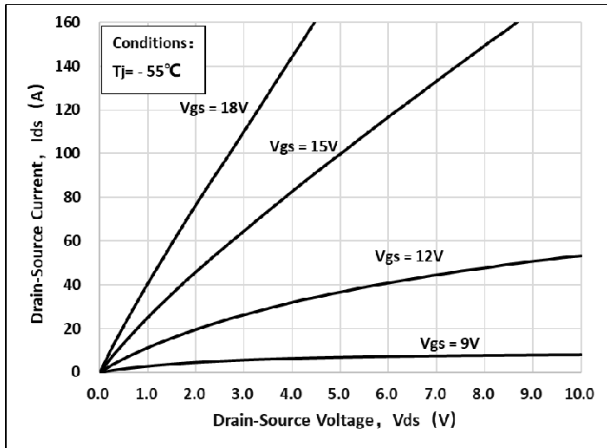


Fig 2. Output Characteristic ($T_J = 25^\circ\text{C}$)

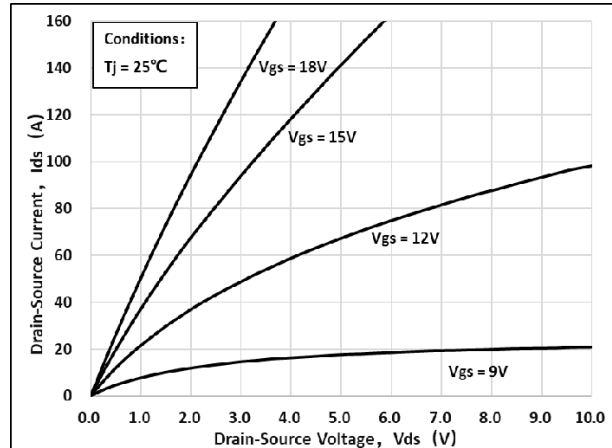


Fig 3. Output Characteristic ($T_J = 175^\circ\text{C}$)

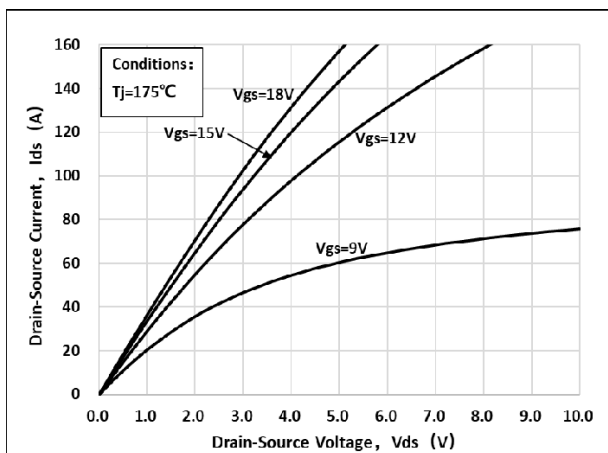


Fig 4: $R_{DS(on)}$ Vs I_{DS} Characteristic

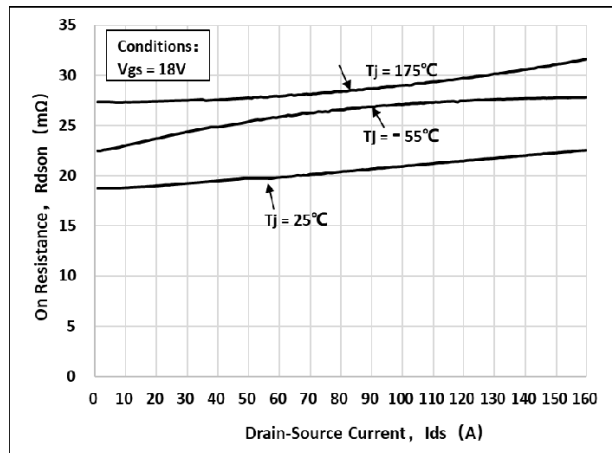


Fig 5: $R_{DS(on)}$ vs. Temperature

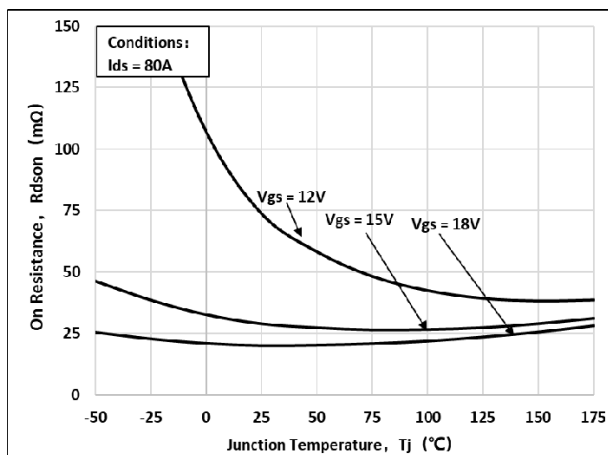


Fig 6: Transfer Characteristic

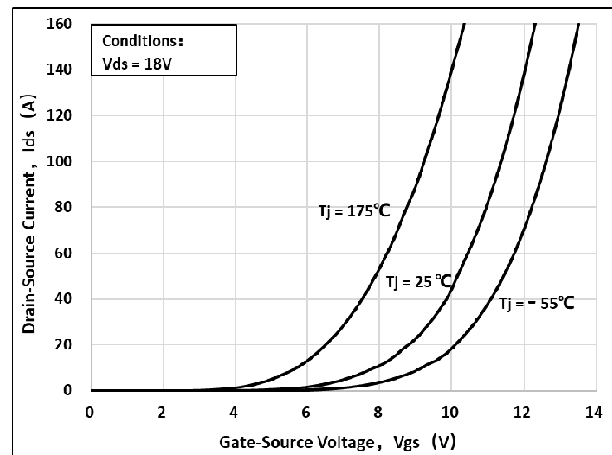




Fig 7: Body-diode Characteristic ($T_J = -55^\circ\text{C}$)

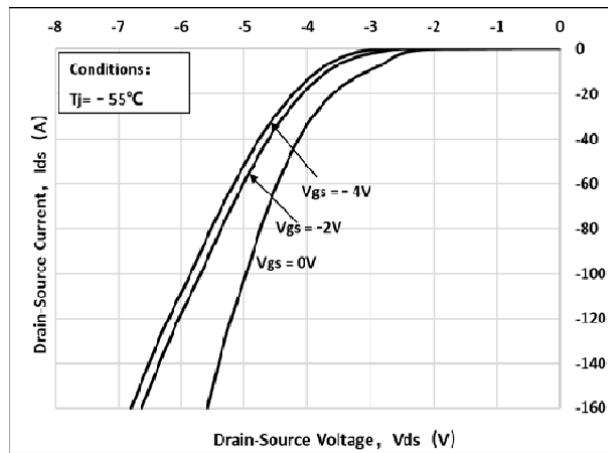


Fig 8: Body-diode Characteristic ($T_J = 25^\circ\text{C}$)

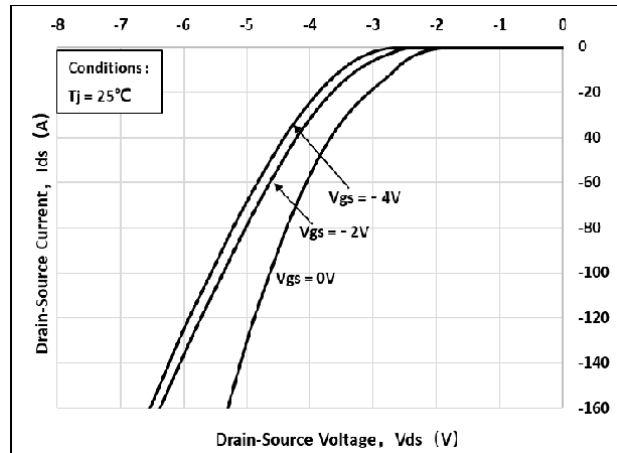


Fig 9: Body-diode Characteristic ($T_J = 175^\circ\text{C}$)

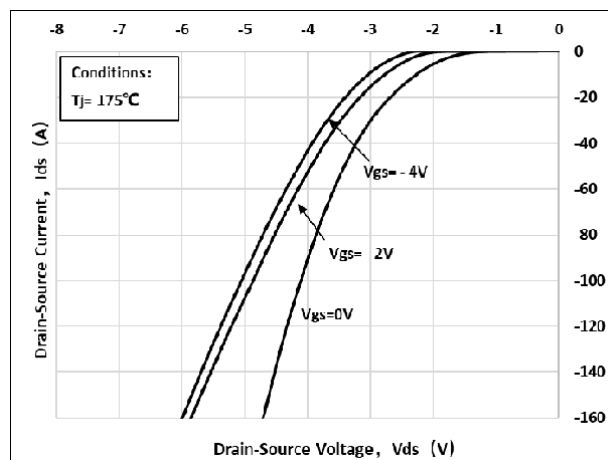


Fig 10: V_{th} Vs T_J Temperature Characteristic

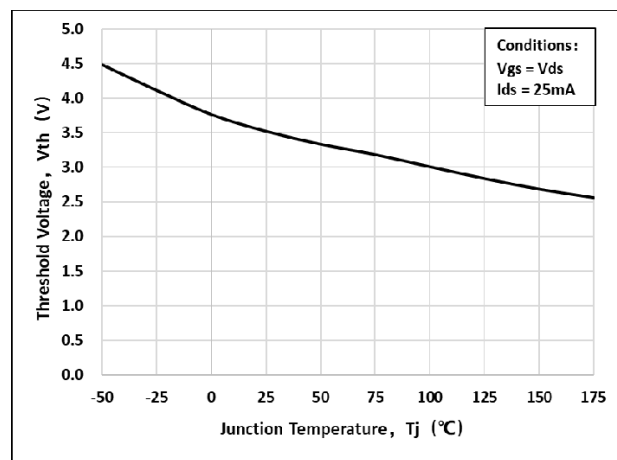


Fig 11: Gate Charge Characteristics

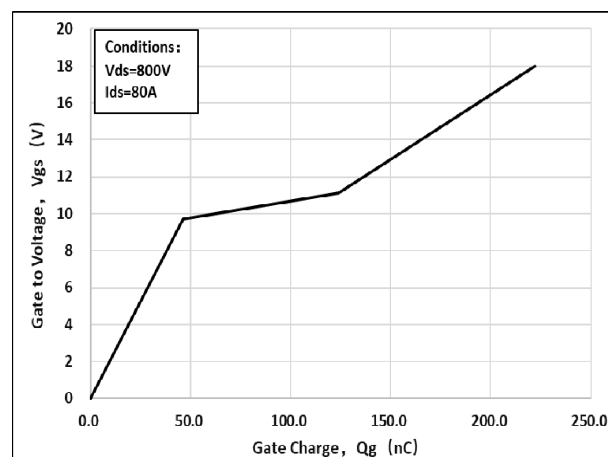


Fig 12: 3rd Quadrant Characteristic ($T_J = -55^\circ\text{C}$)

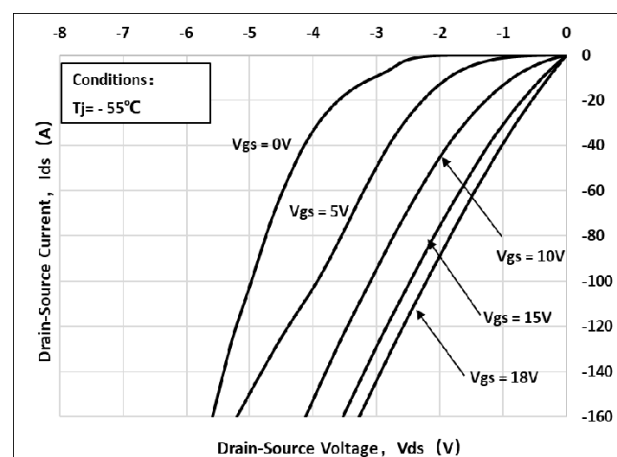




Fig 13: 3rd Quadrant Characteristic($T_J=25^{\circ}\text{C}$)

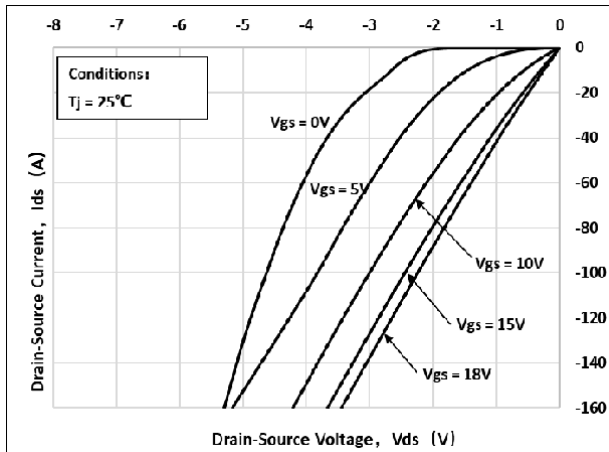


Fig 14: 3rd Quadrant Characteristic($T_J=175^{\circ}\text{C}$)

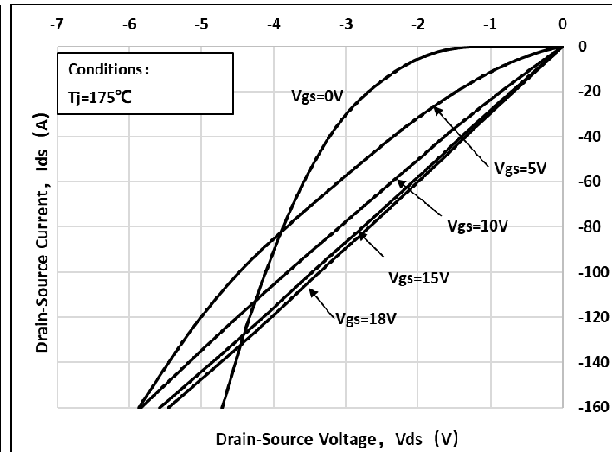


Fig 15: Capacitance Characteristic

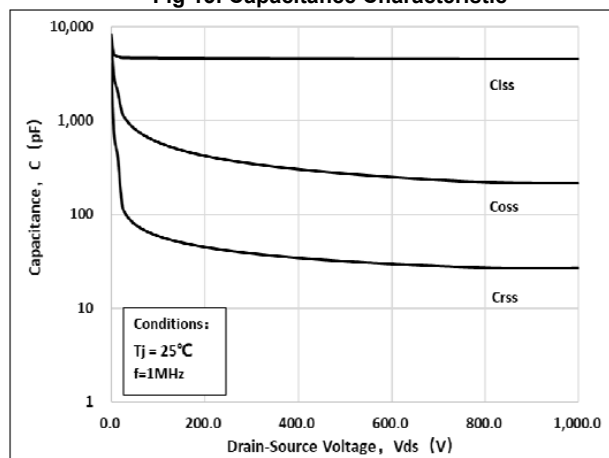


Fig 16: Safe Operating Area

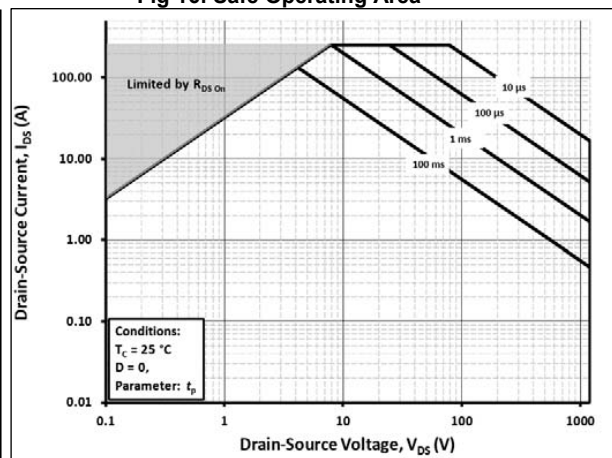
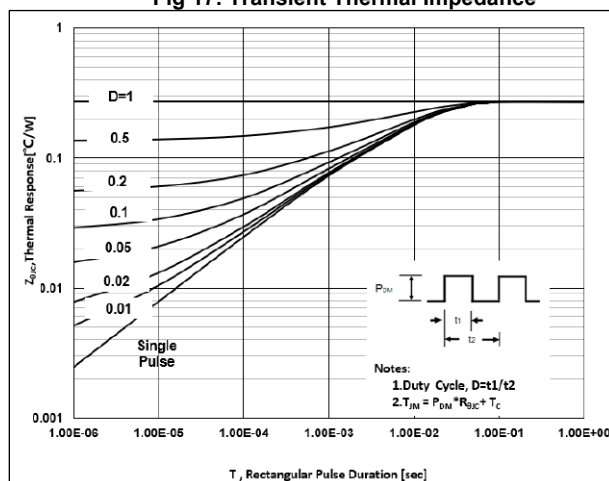


Fig 17: Transient Thermal Impedance





Test Circuit Schematic

Figure A. Definition of switching times

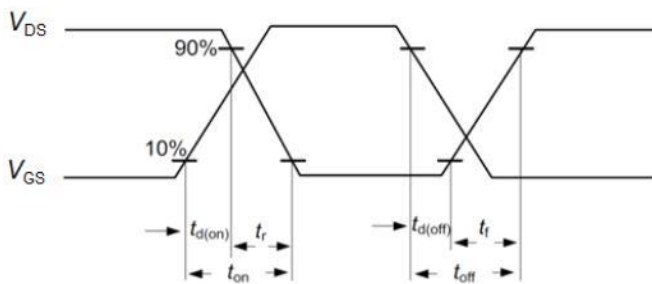


Figure B. Dynamic test circuit

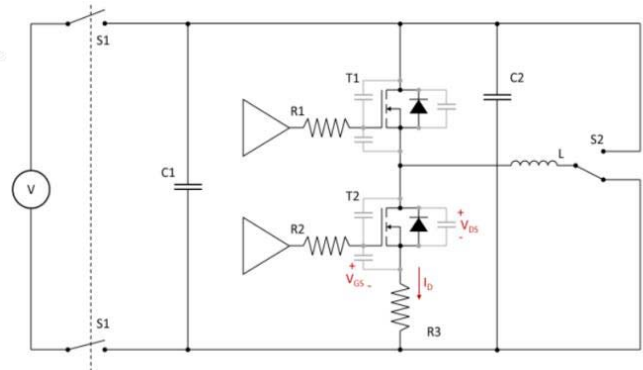


Figure C. Definition of body diodeswitching characteristics

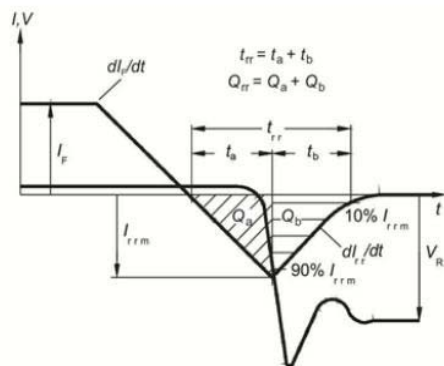
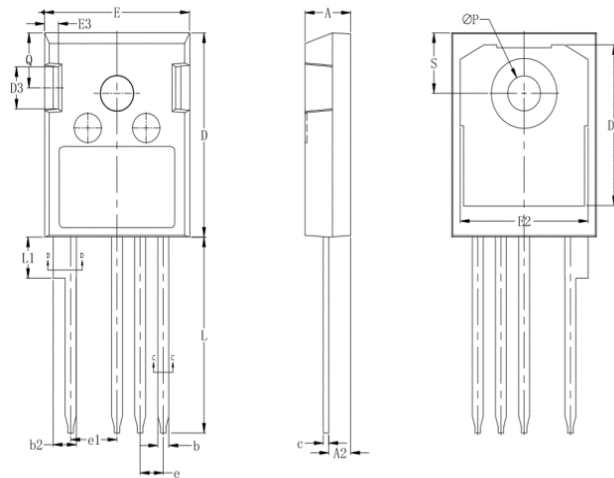


Figure C. Definition of diode switching characteristics



Package Dimensions

Package TO-247-4L



Items	Values(mm)	
	MIN	MAX
A	4.8	5.2
A2	2.2	2.6
b	1.05	1.4
b2	2.4	2.75
c	0.5	0.75
D	20	21.5
D2	15.5	17.2
D3	4	5
E	15.5	16.1
E2	13	15
E3	1	2
e	2.54 BSC.	
e1	5.08 BSC.	
L	19	21
L1	4	4.45
ΦP	3.5	3.7
Q	5.4	5.9
S	5.9	6.4



Attention

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.